



100V NPN MEDIUM POWER TRANSISTOR IN TO252

Features

- BV_{CEO} > 100V
- I_C = 3A High Continuous Collector Current
- I_{CM} = 5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary PNP Type: MJD32CUQ
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MJD31CUQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

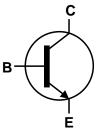
Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (Approximate)

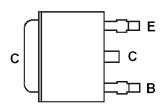




Top View



Device Schematic



Pin Out Configuration Top View

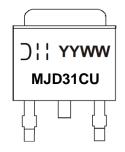
Ordering Information (Note 4)

Part Number	Paakaga	Marking	Reel Size (inches)	Tape Width (mm)	Packing		
Part Number	Package Marking		Reel Size (Inches)	rape width (mm)	Qty.	Carrier	
MJD31CUQ-13	TO252 (DPAK)	MJD31CU	13	16	2,500	Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	120	V
Collector-Emitter Voltage	VCEO	100	V
Emitter-Base Voltage	VEBO	7	V
Continuous Collector Current	Ic	3	A
Peak Pulse Collector Current	I _{CM}	5	A
Continuous Base Current	l _Β	1	A
Power Dissipation	PD	16	W

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		2.60		
Power Dissipation	(Note 6)	PD	2.30	W	
	(Note 7)		1.45		
	(Note 5)		48		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	54		
	(Note 7)		86	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	RøJL	7.8		
Thermal Resistance, Junction to Case	(Note 7)	Rejc	7.3		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 9)

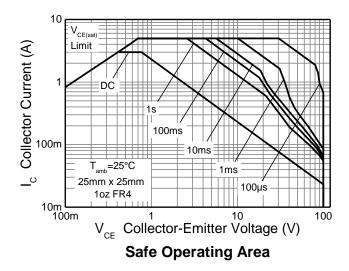
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

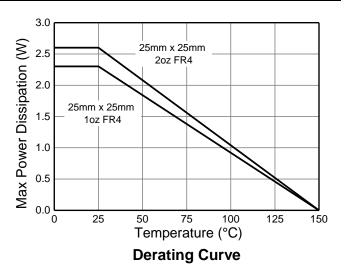
Notes:

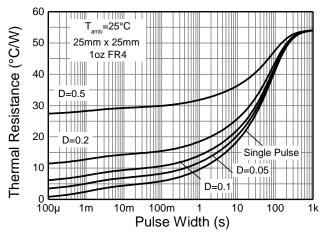
- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.
 7. Same as note (5), except mounted on minimum recommended pad (MRP) layout.
 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

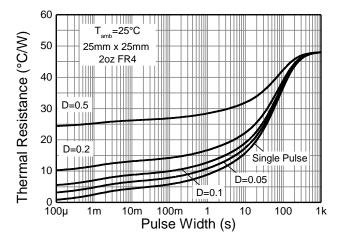


Thermal Characteristics



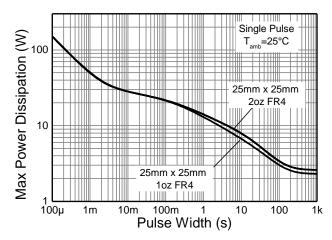






Transient Thermal Impedance

Transient Thermal Impedance



Pulse Power Dissipation



Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	120	_	_	V	Ic = 20μA
Collector-Emitter Breakdown Voltage (Note 10)	BVceo	100	_	_	V	Ic = 30mA
Emitter-Base Breakdown Voltage	BVEBO	7	_	_	V	I _E = 100μA
Collector-Base Cut-off Current	I _{CBO}		_	1	μΑ	V _{CB} = 100V
Collector Cut-off Current	I _{CEO}		_	1	μΑ	$V_{CE} = 60V$
Collector Cut-off Current	I _{CES}		_	1	μΑ	V _{CE} = 100V
Emitter Cut-off Current	I _{EBO}		_	1	μΑ	V _{EB} = 5V
		_	_	300	mV	$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 10)	VCE(sat)	_	_	500	mV	$I_C = 2A$, $I_B = 200mA$
			_	700	mV	$I_C = 3A$, $I_B = 375mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}		_	1.2	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	_	950	mV	Ic = 1A, VcE = 2V
base-Emilier rum-On voltage (Note 10)			_	1.4	V	Ic = 3A, VcE = 4V
DC Current Gain (Note 10)	h	25		_		Vce = 4V, Ic = 1A
DC Current Gain (Note 10)	hFE	10	_	50	_	$V_{CE} = 4V$, $I_C = 3A$
Current Signal Current Gain	H _{fe}	20	_	_	_	$V_{CE} = 10V, I_{C} = 0.5A, f = 1kHz$
Current Gain-Bandwidth Product	f⊤	3	_	_	MHz	Ic = 0.5A, VcE = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

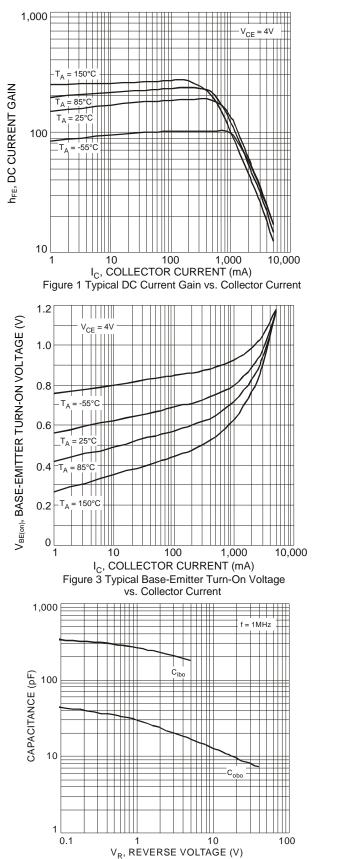
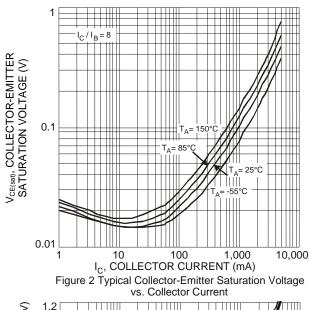


Figure 5 Typical Capacitance Characteristics



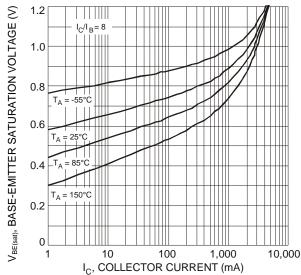


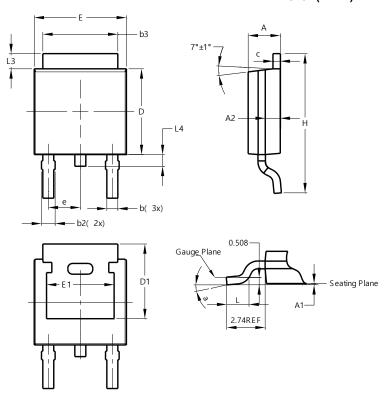
Figure 4 Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

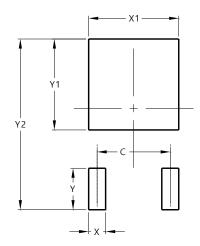


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.50	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21				
е	2.	286 BS	S		
Е	6.45	6.70	6.58		
E1	4.32				
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700



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